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CORRECTION

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Correction: Raw product of rare-earth ore works as a high-k gate insulator for low-voltage operable organic field-effect transistors

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Correction for 'Raw product of rare-earth ore works as a high-k gate insulator for low-voltage operable organic field-effect transistors' by Xue-feng She et al., RSC Adv., 2016, 6, 114593–114598.

The structure of the cyanoethylated pullulan polymer depicted in Fig. 1 was incorrect and the correct structure of the polymer unit is represented below:

R=CH₂CH₂CN or H
CEP

The Royal Society of Chemistry apologises for these errors and any consequent inconvenience to authors and readers.

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